



- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

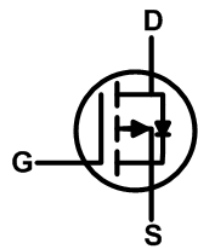
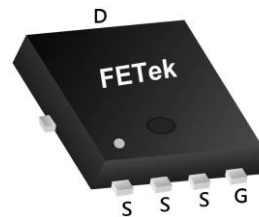
Product Summary

BVDSS	RDSON	ID
-100V	50mΩ	-8A

Description

The FKBA0139 uses advanced trench MOSFET technology to provide excellent $R_{DS(ON)}$ and gate charge for use in a wide variety of other applications.

The FKBA0139 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

PRPAK5X6 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	±20	V
$I_D @ T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-8	A
$I_D @ T_A=100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-6.5	A
I_{DM}	Pulsed Drain Current ²	-45	A
EAS	Single Pulse Avalanche Energy ³	345	mJ
I_{AS}	Avalanche Current	28	A
$P_D @ T_A=25^\circ C$	Total Power Dissipation ⁴	5.5	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ , $t \leq 10s$	---	22	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	1.22	°C/W

**Electrical Characteristics (T_J=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-100	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-8A	---	42	50	mΩ
		V _{GS} =-4.5V , I _D =-6A	---	46	55	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.2	-1.8	-2.5	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-100V , V _{GS} =0V , T _J =25°C	---	---	-1	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-10V , I _D =-10A	---	32	---	S
Q _g	Total Gate Charge	V _{DS} =-80V , V _{GS} =-10V , I _D =-8A	---	92	---	nC
Q _{gs}	Gate-Source Charge		---	17.5	---	
Q _{gd}	Gate-Drain Charge		---	14	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-50V , V _{GS} =-10V , R _G =3.3Ω, I _D =-1A	---	20.5	---	ns
T _r	Rise Time		---	32.2	---	
T _{d(off)}	Turn-Off Delay Time		---	123	---	
T _f	Fall Time		---	63.7	---	
C _{iss}	Input Capacitance	V _{DS} =-25V , V _{GS} =0V , f=1MHz	---	6516	---	pF
C _{oss}	Output Capacitance		---	223	---	
C _{rss}	Reverse Transfer Capacitance		---	125	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current	---	---	-30	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	I _F =-14A , di/dt=-100A/μs ,	---	31.2	---	nS
Q _{rr}	Reverse Recovery Charge	T _J =25°C	---	31.97	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=-25V,V_{GS}=-10V,L=0.88mH,I_{AS}=-28A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

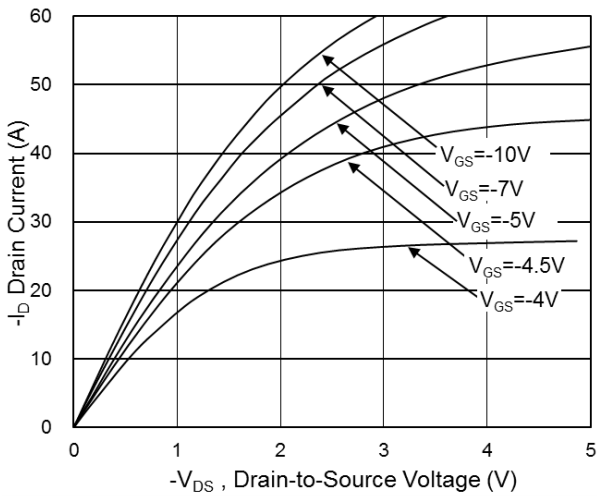


Fig.1 Typical Output Characteristics

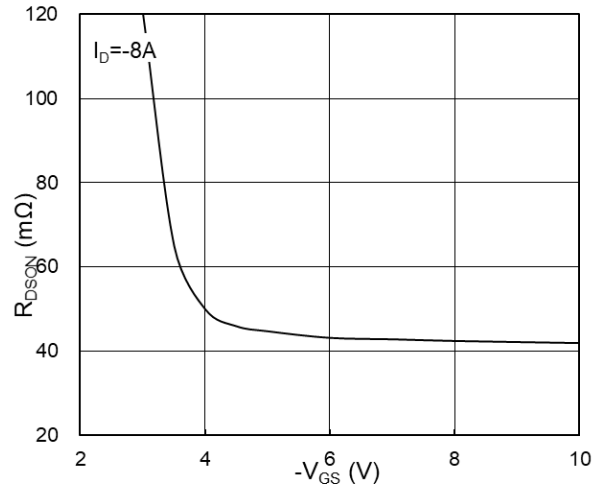


Fig.2 On-Resistance vs G-S Voltage

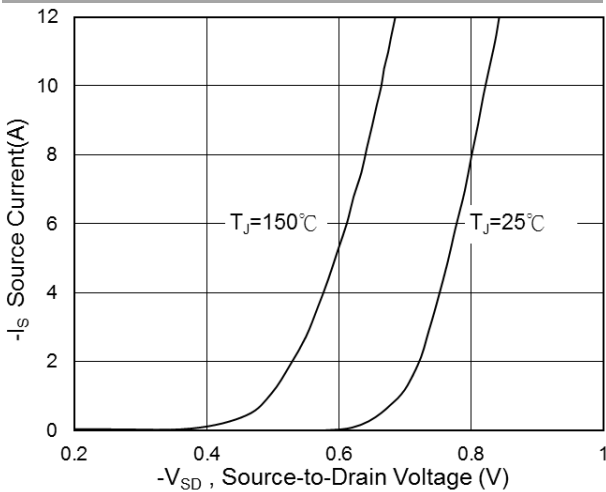


Fig.3 Typical S-D Diode Forward Voltage

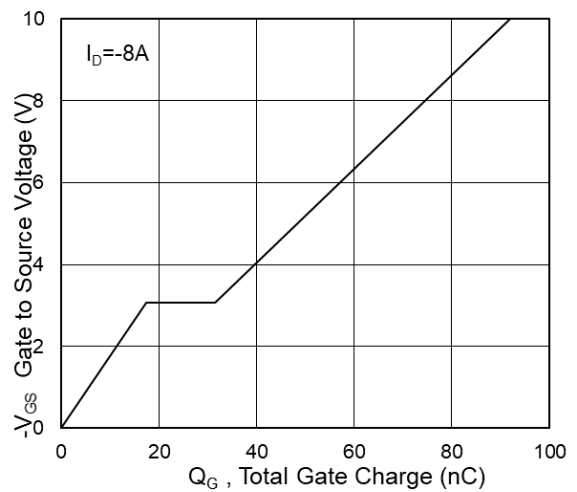


Fig.4 Gate-Charge Characteristics

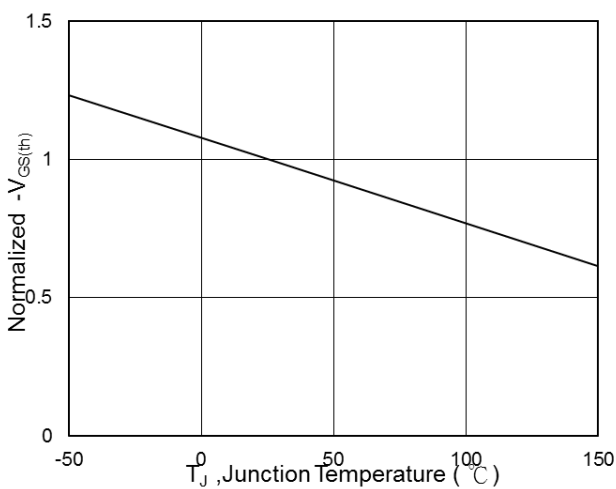


Fig.5 Normalized $V_{GS(th)}$ vs T_J

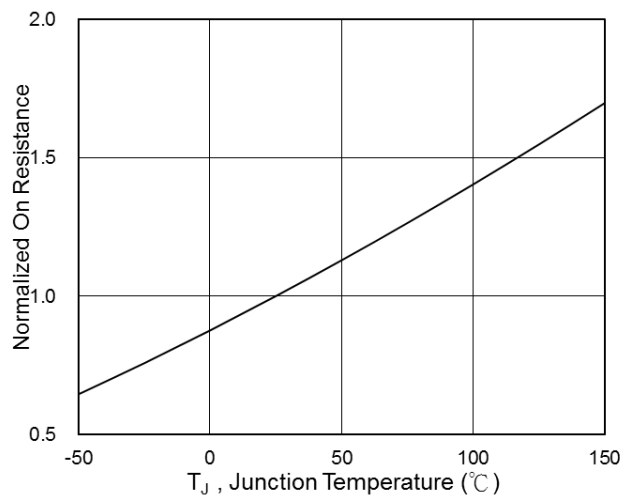


Fig.6 Normalized $R_{DS(on)}$ vs T_J

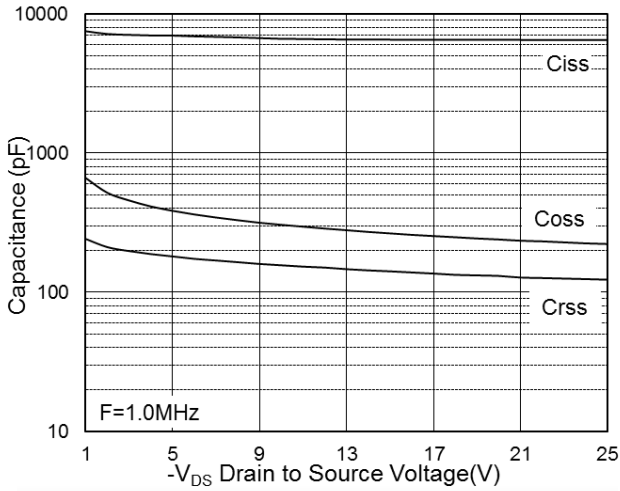


Fig.7 Capacitance

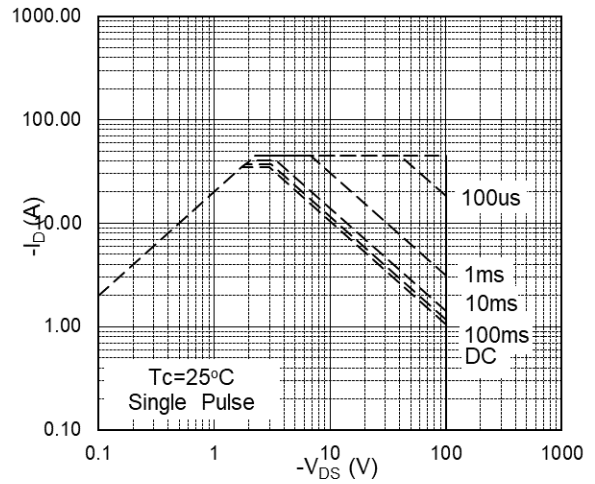


Fig.8 Safe Operating Area

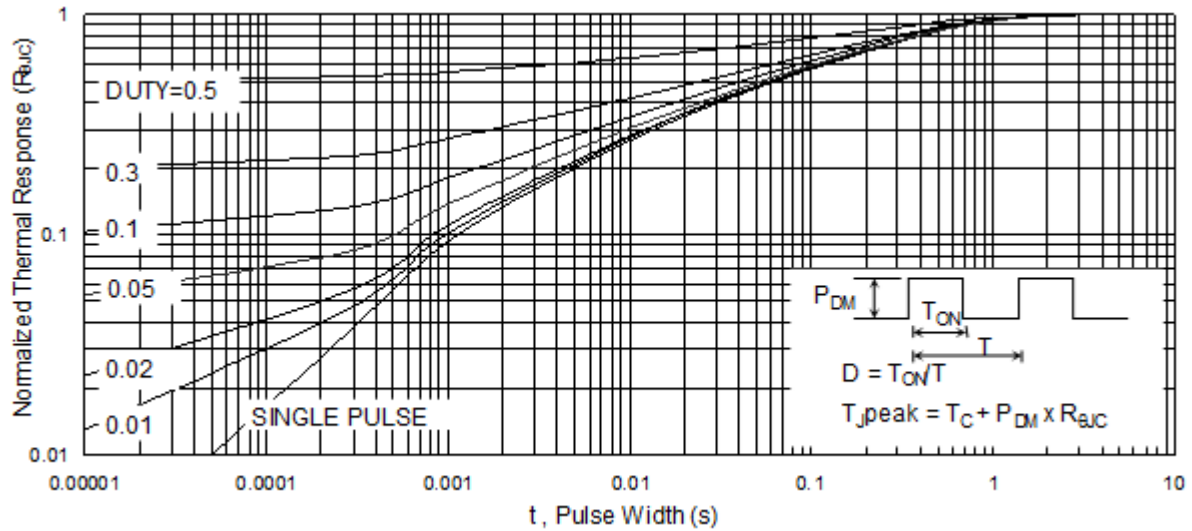


Fig.9 Normalized Maximum Transient Thermal Impedance

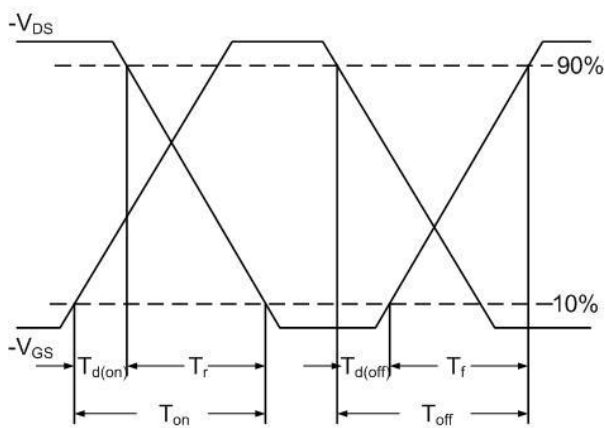


Fig.10 Switching Time Waveform

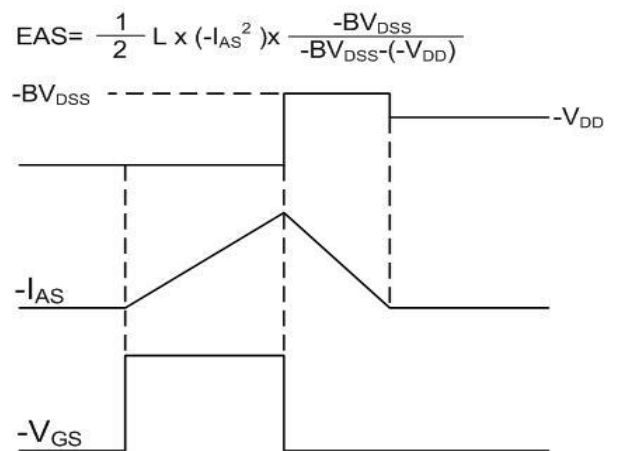


Fig.11 Unclamped Inductive Waveform